

NOT RECOMMENDED FOR NEW DESIGN CONTACT US



AP3512E

18V, 2A SYNCHRONOUS DC-DC BUCK CONVERTER

Description

The AP3512E is a 500kHz fixed frequency, current mode, PWM synchronous buck (step-down) DC-DC converter, capable of driving a 2A load with high efficiency, excellent line and load regulation. The AP3512E exhibits high efficiency at light load. The device integrates N-channel power MOSFET switch with low on-resistance. Current mode control provides fast transient response and cycle-by-cycle current limit.

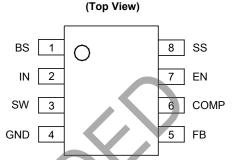
The AP3512E employs complete protection to ensure system security, including output Over Voltage Protection, input Under Voltage Lock Out, programmable Soft-start, Over Temperature Protection and hiccup mode Short Circuit Protection.

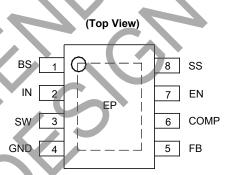
This IC is available in SO-8 and SO-8EP packages.

Features

- Input Voltage Range: 4.5V to 18V
- Fixed 500kHz Frequency
- High Efficiency at Light Load
- Output Current: 2A
- Current Mode Control
- Built-In Over Current Protection
- Built-In Thermal Shutdown Function
- Built-In UVLO Function
- Built-In Over Voltage Protection
- Programmable Soft-Start
- Hiccup Mode SCP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments





SO-8

SO-8EP

Applications

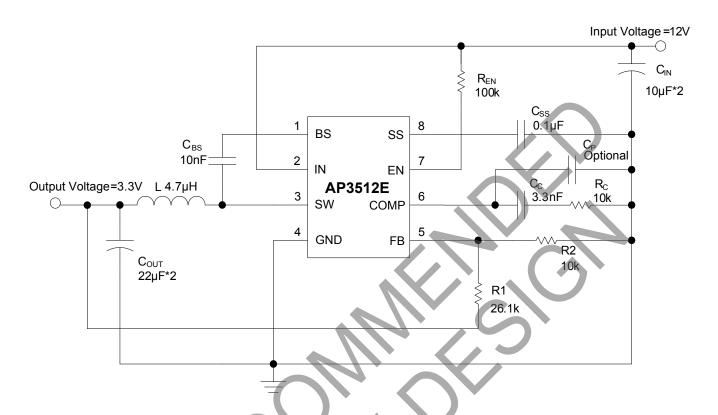
- Monitor
- TV
- STB
- Datacom

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Typical Applications Circuit

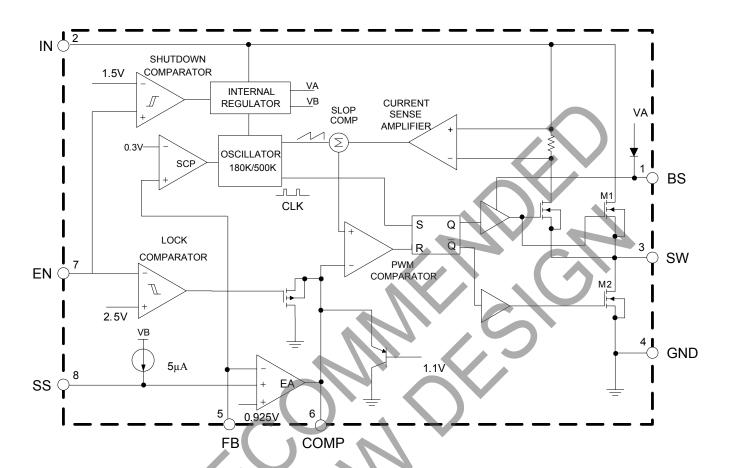


Pin Descriptions

Pin Number	Pin Name	Function
1	BS	Bootstrap pin. A bootstrap capacitor is connected between the BS pin and SW pin. The voltage across the bootstrap capacitor drives the internal high-side NMOS switch.
2	IN	Supply input pin. A capacitor should be connected between the IN pin and GND pin to keep the DC input voltage constant.
3	sw	Power switch output pin. This pin is connected to the inductor and bootstrap capacitor.
4	GND	Ground pin
5	FB	Feedback pin. This pin is connected to an external resistor divider to program the system output voltage. When the FB pin voltage exceeds 1.1V, the over voltage protection is triggered. When the FB pin voltage is below 0.3V, the oscillator frequency is lowered to realize short circuit protection.
6	COMP	Compensation pin. This pin is the output of the transconductance error amplifier and the input to the current comparator. This pin is used to compensate the control loop. Connect a series RC network from this pin to GND pin. In some cases, an additional capacitor from this pin to GND pin is required.
7	EN	Enable Input. EN is a digital input that turns the regulator on or off. Drive EN high to turn on the regulator, drive it low to turn off. Pull up with $100k\Omega$ resistor for automatic startup.
8	SS	Soft-start control input pin. SS controls the soft start period. Connect a capacitor from SS to GND to set the soft-start period. A 0.1µF capacitor sets the soft-start period to 15ms. To disable the soft-start feature, leave SS unconnected.
_	EP	Exposed pad. It should be connected to GND in PCB layout.



Functional Block Diagram





Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Value	Unit
V _{IN}	IN Pin Voltage	-0.3 to 20	V
V _{EN}	EN Pin Voltage	-0.3 to V _{IN}	V
Vsw	SW Pin Voltage	21	V
V _{BS}	BS Pin Voltage	-0.3 to V _{SW} +6	V
V_{FB}	FB Pin Voltage	-0.3 to 6	V
V _{СОМР}	COMP Pin Voltage	-0.3 to 6	V
Vss	SS Pin Voltage	-0.3 to 6	V
TJ	Operating Junction Temperature	+150	°C
T _{STG}	Storage Temperature	-65 to +150	°C
T _{LEAD}	Lead Temperature (Soldering, 10s)	+260	°C
θЈА	Thermal Resistance (Junction to Ambient)	SO-8 105 SO-8EP 60	°C/W
V _{HBM}	ESD (Human Body Model)	2000	V
V _{MM}	ESD (Machine Model)	200	V

Note 4: Stresses greater than those listed under "Absolute Maximum Ratings" can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods can affect device reliability.

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
V _{IN}	Input Voltage	4.5	18	V
TA	Operating Ambient Temperature	-40	+85	°C



SUPPLY VOLTAGE (IN PIN) V _N Input Voltage — 4.5 — 18 V I _O Quiescent Current V _{FB} =IV, V _{EN} =3.3V — 1.2 1.4 mA Isston Shutdown Supply Current V _{EN} =0V — 0.1 1.0 µA UNDER VOLTAGE LOCKOUT V _{IVA} O Input UVI, O Threshold V _{IN} Rising 3.65 4.0 4.25 V EN Shutdown Threshold Voltage — 0.2 — V EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Shutdown Threshold Voltage — 2.2 2.5 2.7 V — EN Lockout Hysteresis — — 2.10 — m/V VFBOY Feedback Solidate Threshold Voltage —	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Io Quiescent Current VFE=1V, VEN=3.3V - 1.2 1.4 mA Isrien Shutdown Supply Current VEN=0V - 0.1 1.0 μA UNDER VOLTAGE LOCKOUT	SUPPLY VOLTA	AGE (IN PIN)					
Issien Shutdown Supply Current Ven=0V	V _{IN}	Input Voltage	_	4.5	_	18	V
UNDER VOLTAGE LOCKOUT	IQ	Quiescent Current	V _{FB} =1V, V _{EN} =3.3V	_	1.2	1.4	mA
Vuvio Input UVLO Threshold Vin Rising 3.65 4.0 4.25 V Vin Vin Input UVLO Hysteresis	I _{SHDN}	Shutdown Supply Current	V _{EN} =0V	_	0.1	1.0	μA
No.	UNDER VOLTA	GE LOCKOUT					
EN Shutdown Threshold Voltage	V _{UVLO}	Input UVLO Threshold	V _{IN} Rising	3.65	4.0	4.25	V
EN Shutdown Threshold Voltage	V _{HYS}	Input UVLO Hysteresis	_	. (0.2	_	V
— EN Shutdown Threshold Voltage Hysteresis (Note 5) — — 350 — mV — EN Lockout Threshold Voltage — 2,2 2,5 2,7 V — EN Lockout Hysteresis — — 210 — mV VOLTAGE REFERENCE (FB PIN) VFBDV Feedback Voltage — 0,907 0,925 0,943 V VFBDV Feedback Over Voltage Threshold — — 1.1 — V VFBDV Feedback Bias Current VFBDV — 0.1 — 0.1 µA MOSFET RosonH High-Side Switch On-resistance (Note 6) Isw=0.2A and 0.7A — 100 — mΩ CURRENT LIMIT It Lawrent Limit Viv=102 And 0.7A — 100 — mΩ LEAKH High-Side Switch Chrest Limit — 4.3 5.6 — A — — — —	ENABLE (EN PI	N)			-		
- (Note 5)	_	EN Shutdown Threshold Voltage	_	1.1	1.5	2	V
— EN Lockout Hysteresis	_		- (-	350	_	mV
VOLTAGE REFERENCE (FB PIN) VFB Feedback Voltage — 0.907 0.925 0.943 V VFBOV Feedback Over Voltage Threshold — — 1.1 — V IFB Feedback Bias Current VFB=1V —0.1 — 0.1 µA MOSFET ROSONH High-Side Switch On-resistance (Note ®) Isw=0.2A and 0.7A — 100 — mΩ CURRENT LIMIT High-Side Switch Corrent Limit VIN=18V, VEN=0V, VSW=0V — 0.1 10 µA I_LIMH High-Side Switch Current Limit — 4.3 5.6 — A I_LIML Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR — 410 500 590 kHz fosc1 Oscillator Frequency — — 410 500 590 kHz DMAX Maximum Duty Cycle VFB=0.85V — — 90	_	EN Lockout Threshold Voltage	-	2.2	2.5	2.7	V
VFB Feedback Voltage - 0.907 0.925 0.943 V VFBOV Feedback Over Voltage Threshold - - 1.1 - V IFB Feedback Bias Current VFB=IV -0.1 - 0.1 µA MOSFET ROSONH High-Side Switch On-resistance (Note 6) Isw=0.2A and 0.7A - 100 - mΩ CURRENT LIMIT High-Side Switch Leakage Current VIN=18V, VEN=0V, V	_	EN Lockout Hysteresis	$\forall I$	-	210	_	mV
VFBOV Feedback Over Voltage Threshold — — — 1.1 — V IFB Feedback Bias Current VFB=1V — 0.1 — 0.1 µA MOSFET ROSONH High-Side Switch On-resistance (Note 6) Isw=0.2A and 0.7A — 100 — mΩ ROSONL Low-Side Switch On-resistance (Note 6) Isw=0.2A and -0.7A — 100 — mΩ CURRENT LIMIT ILEAKH High-Side Switch Leakage Current VIN=18V, VEN=0V, VSW=0V — 0.1 10 µA ILIMI Low-Side Switch Current Limit — 4.3 5.6 — A ILIMI Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR Fosc1 Oscillator Frequency — 410 500 590 kHz Fosc2 Short Circuit Oscillator Frequency — 410 500 590 kHz DMAX Maximum Duty Cycle VFB=0.85V — 90 — % DMIN Minimum Duty Cycle VFB=1V — — 0 % ERROR AMPLIFIER AEA Error Amplifier Voltage Gain (Note 5) — — 400 — V/V GEA Error Amplifier Transconductance — — 400 — V/V GEA Error Amplifier Transconductance — — — 400 — V/V Hold — —	VOLTAGE REF	ERENCE (FB PIN)					
IFB Feedback Bias Current VFB=1V -0.1 -0.1 μA	V_{FB}	Feedback Voltage	-	0.907	0.925	0.943	V
MOSFET RDSONH High-Side Switch On-resistance (Note 6) Isw=0.2A and 0.7A — 100 — mΩ	V_{FBOV}	Feedback Over Voltage Threshold	- \	_	1.1	_	V
RDSONH High-Side Switch On-resistance (Note 6) Isw=0.2A and 0.7A — 100 — mΩ	I _{FB}	Feedback Bias Current	V _{FB} =1V	-0.1	_	0.1	μA
RDSONL Low-Side Switch On-resistance (Note 6) I _{SW} =-0.2A and -0.7A — 100 — mΩ CURRENT LIMIT ILEAKH High-Side Switch Leakage Current VIN=18V, VEN=0V, VVV, VEN=0V, VEN=0V, VEN=0V, VEN=0V, VVV, VEN=0V, VEN=0V, VEN=0V, VEN=0V, VVV, VEN=0V, VEN=0V, VEN=0V, VEN=0V, VEN=0V, VEN=0V, VEN=0V, VEN=0V, VVV, VEN=0V, VEN=	MOSFET						
CURRENT LIMIT ILEAKH High-Side Switch Leakage Current VIN=18V, VEN=0V, VSW=0V, VSW=0V, VSW=0V, VSW=0V, VSW=0V — 0.1 10 μA ILIMH High-Side Switch Current Limit — 4.3 5.6 — A ILIML Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR f OSC1 Oscillator Frequency — 410 500 590 kHz f OSC2 Short Circuit Oscillator Frequency — — 180 — kHz DMAX Maximum Duty Cycle VFB=0.85V — 90 — % DMIN Minimum Duty Cycle VFB=1V — — 0 % ERROR AMPLIFIER AEA Error Amplifier Voltage Gain (Note 5) — — 400 — V/V GEA Error Amplifier Transconductance — — 800 — µAVV	R _{DSONH}	High-Side Switch On-resistance (Note 6)	I _{SW} =0.2A and 0.7A	_	100	_	mΩ
I_LEAKH	R _{DSONL}	Low-Side Switch On-resistance (Note 6)	I _{SW} =-0.2A and -0.7A	_	100	_	mΩ
ILIMH	CURRENT LIMI		•				
I _{LIML} Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR f _{OSC1} Oscillator Frequency — 410 500 590 kHz f _{OSC2} Short Circuit Oscillator Frequency — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V G _{EA} Error Amplifier Transconductance — — 800 — µA/V	ILEAKH	High-Side Switch Leakage Current		_	0.1	10	μΑ
SWITCHING REGULATOR f _{OSC1} Oscillator Frequency — 410 500 590 kHz f _{OSC2} Short Circuit Oscillator Frequency — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V G _{EA} Error Amplifier Transconductance — — 800 — µA/V	Ішмн	High-Side Switch Current Limit	_	4.3	5.6	_	Α
f _{OSC1} Oscillator Frequency — 410 500 590 kHz f _{OSC2} Short Circuit Oscillator Frequency — — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V G _{EA} Error Amplifier Transconductance — — 800 — µA/V	I _{LIML}	Low-Side Switch Current Limit	From drain to source	_	50	_	mA
f _{OSC2} Short Circuit Oscillator Frequency — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V G _{EA} Error Amplifier Transconductance — 800 — μΑ/V	SWITCHING RE	GULATOR					
D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V G _{EA} Error Amplifier Transconductance — 800 — µA/V	fosc1	Oscillator Frequency	_	410	500	590	kHz
D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V G _{EA} Error Amplifier Transconductance — 800 — μΑ/V	fosc2	Short Circuit Oscillator Frequency	_	_	180	_	kHz
ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V G _{EA} Error Amplifier Transconductance — 800 — μΑ/V	D_{MAX}	Maximum Duty Cycle	V _{FB} =0.85V	_	90	_	%
A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V G _{EA} Error Amplifier Transconductance — — 800 — μΑ/V	D _{MIN}	Minimum Duty Cycle	V _{FB} =1V	_	_	0	%
G _{EA} Error Amplifier Transconductance — — 800 — μΑ/V	ERROR AMPLIE	FIER					
	A _{EA}	Error Amplifier Voltage Gain (Note 5)	_	_	400	_	V/V
G _{CS} COMP to Current Sense Transconductance — — 5.2 — A/V	GEA	Error Amplifier Transconductance	_	_	800	_	μΑ/V
	Gcs	COMP to Current Sense Transconductance	_	_	5.2	_	A/V



Electrical Characteristics (continued) (V_{IN}=V_{EN}=12V, V_{OUT}=3.3V, T_A=+25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
THERMAL SHUTDOWN						
T _{OTSD}	Thermal Shutdown (Note 5)	_	_	+160	_	°C
T _{HYS}	Thermal Shutdown Hysteresis (Note 5)	_	_	+30	-	°C
SOFT START (SS PIN)						
tss	Soft-Start Time (Note 5)	C _{SS} =0.1µF	_	15	_	ms
_	Soft-Start Current	_		5	_	μΑ

Notes: 5. Not tested, guaranteed by design.

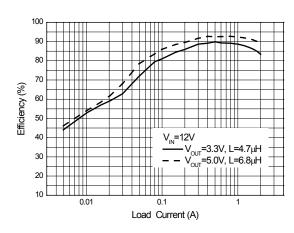
6.
$$R_{DS(ON)} = \frac{V_{SW1} - V_{SW2}}{I_{SW1} - I_{SW2}}$$



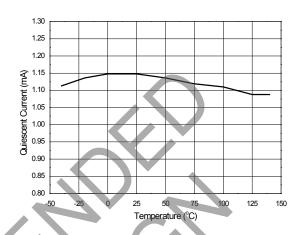


Performance Characteristics (V_{IN}=12V, V_{OUT}=3.3V, L=4.7µH, T_A=+25°C, unless otherwise noted.)

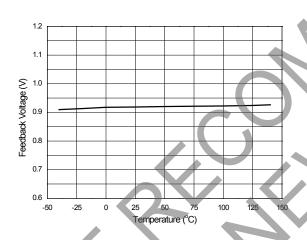
Efficiency vs. Load Current



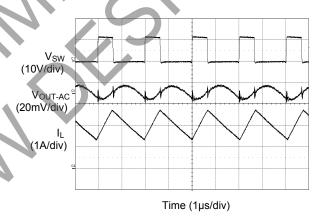
Quiescent Current vs. Temperature



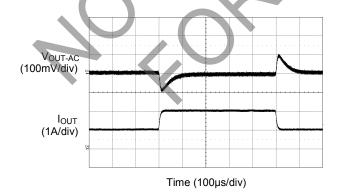
Feedback Voltage vs. Temperature



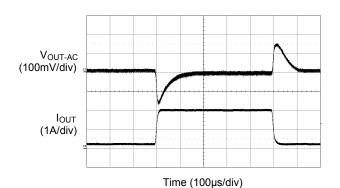
Output Ripple (I_{OUT}=2A)



Load Transient Response (I_{OUT}=1A to 2A)



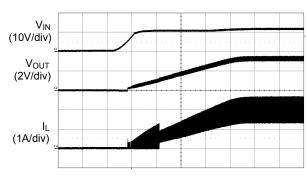
Load Transient Response (I_{OUT}=0.2A to 2A)





Performance Characteristics (continued) (V_{IN}=12V, V_{OUT}=3.3V, L=4.7µH, T_A=+25°C, unless otherwise noted.)

Power On from V_{IN} (I_{OUT}=2A)



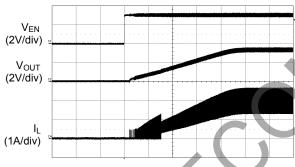
Time (3.20ms/div)

Power Off from V_{IN} (I_{OUT}=2A)



Time (3.20ms/div)

Power On from EN (I_{OUT}=2A)



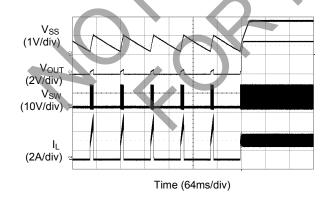
Time (3.20ms/div)

Power Off from EN (I_{OUT}=2A)

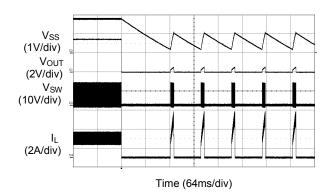


Time (3.20ms/div)

Short Circuit Protection (I_{OUT}=2A)

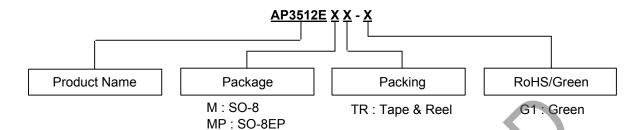


Short Circuit Protection Recovery (I_{OUT}=2A)





Ordering Information



Package (Note 8)	Temperature Range	Part Number	Packing	Status (Note 7)
SO-8	-40 to +85°C	AP3512EMTR-G1	4000/Tape & Reel	In production
SO-8EP	-40 to +85°C	AP3512EMPTR-G1	4000/Tape & Reel	In production

Notes: 7. All Tube versions are End of Life with replacement in Tape & Reel versions.

8. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

(1) SO-8



(Top View)

First and Second Lines: Logo and Marking ID

Third Line: Date Code

Y: Year

WW: Work Week of Molding

A: Assembly Site Code XX: 7th and 8th Digits of Batch Number

(2) SO-8EP





First and Second Lines: Logo and Marking ID

Third Line: Date Code

Y: Year

WW: Work Week of Molding

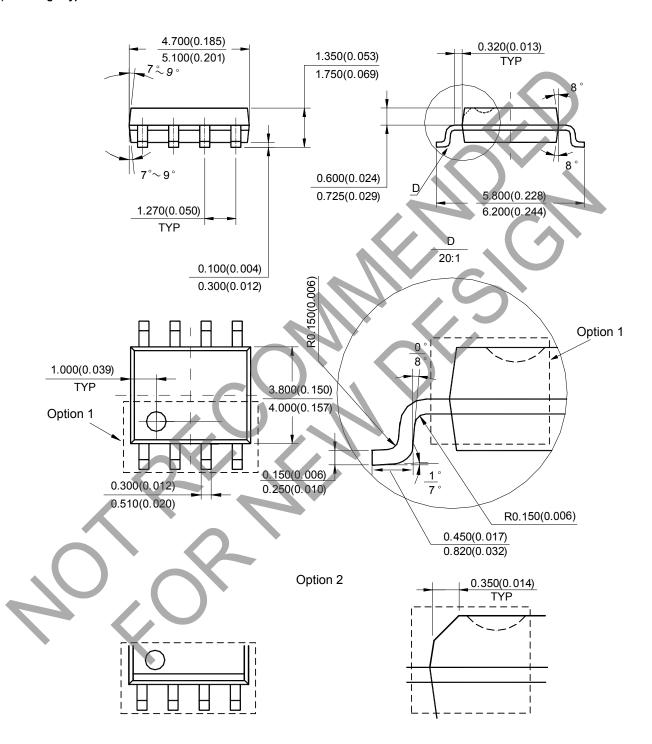
A: Assembly Site Code XX: 7th and 8th Digits of Batch Number



Package Outline Dimensions (All dimensions in mm(inch).)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SO-8



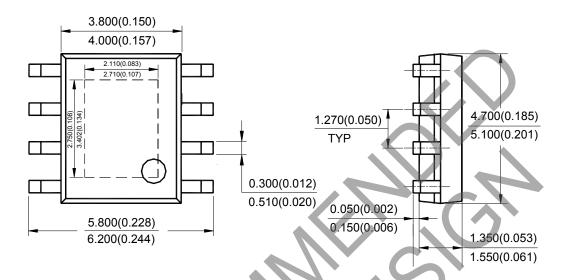
Note: Eject hole, oriented hole and mold mark is optional.

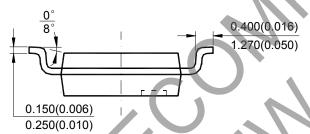


Package Outline Dimensions (continued. All dimensions in mm (inch).)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(2) Package Type: SO-8EP





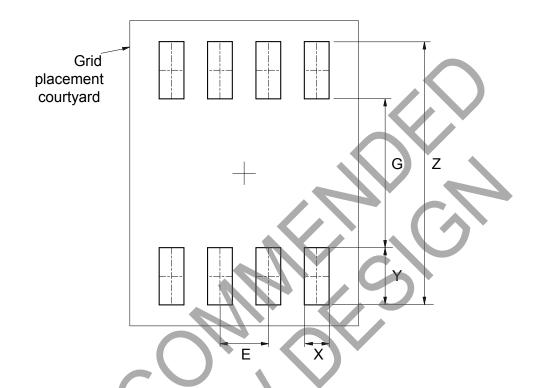
Note: Eject hole, oriented hole and mold mark is optional.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SO-8



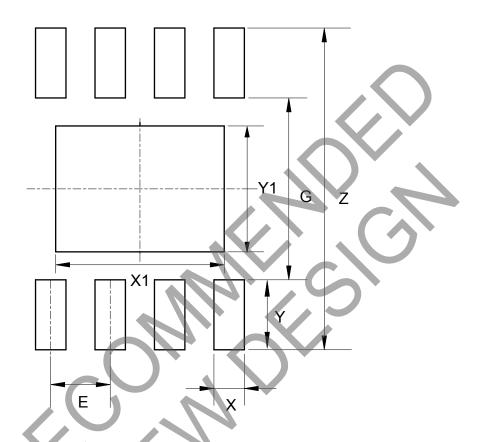
Dimensions	Z	G	X	Y	E
	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	6.900/0.272	3.900/0.154	0.650/0.026	1.500/0.059	1.270/0.050



Suggested Pad Layout (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(2) Package Type: SO-8EP



Dimensions	Z (mm)/(inch)	G (mm)/(inch)	(mm)/(inch)	Y (mm)/(inch)	X1 (mm)/(inch)	Y1 (mm)/(inch)	E (mm)/(inch)
Value	6.900/0.272	3.900/0.154	0.650/0.026	1.500/0.059	3.600/0.142	2.700/0.106	1.270/0.050



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- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

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